

BC212L



TO-92

PNP General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300mA. Sourced from Process 68.

Absolute Maximum Ratings* TA=

T_{A = 25°C} unless otherwise noted

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Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	50	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	300	mA
T _{J, Tstg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

 $^{^{\}star}$ These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 $^{\circ}\text{C}.$
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Characteristic	Max	Units
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _θ JC	Thermal Resistance, Junction to Case		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP	General	Purpose	Amplifier

(continued)

Electrical Characteristics

T_{A = 25°C} unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 2 mA	50		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	ΙΕ = 10 μΑ	5		V
СВО	Collector Cutoff Current	V _{CB} = 30V		15	nA
EBO	Emitter Cutoff Current	V _{EB} = 4V		15	nA
ON CHAR	ACTERISTICS*				•
JEE	DC Current Gain	$I_C = 10 \text{ uA}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$	40 60	300	
√ _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 100 mA, I _B = 5 mA		0.6	V
/ _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 100 mA, I _B = 5 mA		1.1	V
/ _{BE(on)}	Base-Emitter On Voltage	I _C = 2 mA, V _{CE} = 5 V	0.6	0.72	V
SMALL S	IGNAL CHARACTERISTICS		1		
C _{ob}	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		10	pF
η _{fe}	Small Signal Current Gain	I _C = 2 mA,V _{CE} = 5 V, f=1kHz	60		-
NF	Noise Figure	I _C = 200 uA,V _{CE} = 5 V, f=1kHz, Rg=2KOhms,BW=200Hz		10	dB
Т	Current Gain-Bandwidth Product	VCE=5V, IC=10mA,f=100MHz	200		MHz

*Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

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